AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) A stencil mask comprising:

a conductive thin film having a plurality of first openings having a first region and a second region peripheral of the first region, first openings being provided in the first region;

an insulating film formed ~~in a region of~~ on the conductive thin film excluding the first openings;

a conductive support formed on the insulating film, the conductive support having a second opening corresponding to the first openings;

a third opening formed in one of the conductive thin film and the conductive support and the insulating film; and

a conducting member formed ~~so as to replace a portion of the insulating film and which connects~~ in the third opening excluding an inner wall of the first openings, the conducting member connecting the conductive support and the conductive thin film electrically~~,~~

~~wherein one of the conductive thin film and the conductive support has a second opening in which the conducting member is formed, the second opening being positioned in a region excluding the plurality of first openings~~.

2. (Original) The stencil mask according to claim 1, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.

3. (Original) The stencil mask according to claim 1, wherein the conductive thin film and the conductive support are made of silicon.

4. (Original) The stencil mask according to claim 1, wherein the conducting member is made of tungsten.

5. (Original) The stencil mask according to claim 1, further comprising silicon or silicide formed on the surface of the conducting member.

6. (Original) The stencil mask according to claim 1, wherein the conducting member is formed in the conductive support.

7. (Original) The stencil mask according to claim 1, wherein the conducting member is formed in the conductive thin film.

8. (Original) The stencil mask according to claim 1, wherein the conducting member is formed on and in the conductive thin film.

9. (Currently Amended) A stencil mask comprising:

a conductive thin film having ~~an inside~~ a first region and ~~an outside~~ a second region peripheral of the first region, the ~~inside~~ first region including a plurality of first openings so as to form a mask pattern~~, and the outside region being outside the mask pattern~~;

an insulating film ~~which is~~ formed on ~~the outside region on a first side of~~ the conductive thin film excluding the first openings;

a conductive support ~~which is~~ formed on the insulating film, the conductive support having a second opening corresponding to the first openings;

a ~~second~~ third opening ~~in the inside region~~ formed in the conductive support and the insulating film, the third opening being positioned in the second region;

~~a third opening in the outside region formed in the conductive support and the insulating film;~~ and

a conducting member ~~which is~~ provided in the third opening excluding an inner wall of the first openings, the conducting member ~~and which connects~~ connecting the conductive thin film and the conductive support electrically.

10. (Original) The stencil mask according to claim 9, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.

11. (Original) The stencil mask according to claim 9, wherein the conductive thin film and the conductive support are made of silicon.

12. (Original) The stencil mask according to claim 9, wherein the conducting member is made of tungsten.

13. (Original) The stencil mask according to claim 9, further comprising silicon or silicide formed on the surface of the conducting member.

14. (Currently Amended) A stencil mask comprising:

a conductive thin film having ~~an inside~~ a first region and ~~an outside~~ a second region peripheral of the first region, the ~~inside~~ first region including a plurality of first openings so as to form a mask pattern~~, and the outside region being outside the mask pattern~~;

an insulating film formed on the ~~outside~~ second region of the conductive thin film;

a conductive support formed on the insulating film, the conductive support having a second opening corresponding to the first openings;

a ~~second~~ third opening ~~in the outside region~~ formed in the conductive thin film and the insulating film, the third opening being positioned in the second region; and

a conducting member ~~which is~~ formed in the second opening ~~and which connects~~ excluding an inner wall of the first openings, the conducting member connecting the conductive thin film and the conductive support electrically.

15. (Original) The stencil mask according to claim 14, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.

16. (Original) The stencil mask according to claim 14, wherein the conductive thin film and the conductive support are made of silicon.

17. (Original) The stencil mask according to claim 14, wherein the conducting member is made of tungsten.

18. (Original) The stencil mask according to claim 14, further comprising silicon or silicide formed on the surface of the conducting member.

19. (Currently Amended) A stencil mask comprising:

a conductive thin film having ~~an inside~~ a first region and ~~an outside~~ a second region peripheral of the first region, the ~~inside~~ first region including a plurality of

first openings so as to form a mask pattern~~, and the outside region being outside the mask pattern~~;

an insulating film formed on the ~~outside~~ second region;

a conductive support formed on the insulating film, the conducting support having a second opening corresponding to the first openings;

a ~~second~~ third opening ~~in the outside region~~ formed in the conductive thin film and the insulating film, the third opening being positioned in the second region; and

a conducting member ~~which is~~ formed on the surface of the conductive thin film and in the ~~second~~ third opening ~~and which connects~~ excluding an inner wall of the first openings, the conducting member connecting the conductive thin film and the conductive support electrically.

20. (Original) The stencil mask according to claim 19, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.

21. (Original) The stencil mask according to claim 19, wherein the conductive thin film and the conductive support are made of silicon.

22. (Original) The stencil mask according to claim 19, wherein the conducting member is made of tungsten.

23. (Original) The stencil mask according to claim 19, further comprising silicon or silicide formed on the surface of the conducting member.

24. (Currently Amended) A mask forming substrate comprising:

a conductive thin film having ~~an inside~~ a first region and ~~an outside~~ a second region peripheral of the first region;

an insulating film formed on the conductive thin film in the second region excluding the first openings;

a conductive support formed on the insulating film, the conducting support having a second opening corresponding to the first openings;

~~an~~ a third opening ~~in the outside region~~ formed in the conductive support and the insulating film; and

a conducting member ~~which is~~ formed in the third opening excluding an inner wall of the first openings, ~~and which connects~~ the conducting member connecting the conductive thin film and the conductive support electrically.

25. (Previously Presented) The mask forming substrate according to claim 24, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.

26. (Original) The mask forming substrate according to claim 24, wherein the conductive thin film and the conductive support are made of silicon.

27. (Original) The stencil mask according to claim 24, wherein the conducting member is made of tungsten.

28. (Currently Amended) A mask forming substrate comprising:

a conductive thin film having ~~an inside~~ a first region as an opening formation region and ~~an outside~~ a second region peripheral of the first region;

an insulating film formed on the conductive thin film;

a conductive support formed on the insulating film;

an opening ~~in the outside region~~ formed in the conductive thin film and the insulating film corresponding to a part of the second region; and

a conducting member ~~which is~~ formed on the conductive thin film and in the opening ~~and which connects~~, the conducting member connecting the conductive thin film and the conductive support electrically.

29. (Withdrawn) A stencil mask manufacturing method comprising:

making a plurality of openings in a first region of a conductive thin film of an SOI substrate which includes a substrate, an insulating film formed on the substrate,

and the conductive thin film with the first region and a second region formed on the insulating film;

forming a support by removing the substrate in a region corresponding to the first region of the conductive thin film and the substrate in a part of a region corresponding to the second region of the conductive thin film;

removing the insulating film corresponding to the first region and second region exposed as a result of the formation of the support; and

forming a conducting member electrically connecting the substrate and the conductive thin film in a region corresponding to the second region from which the insulating film has been removed, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film.

30. (Withdrawn) A stencil mask manufacturing method comprising:

making first openings in a first region of and a second opening in a second region of a conductive thin film of an SOI substrate which includes a substrate, an insulating film formed on the substrate, and the conductive thin film with the first region and the second region formed on the insulating film;

forming a support by removing the substrate in a region corresponding to the first region;

removing the insulating film exposed as a result of the formation of the support; and

forming a conducting member in the second opening of the conductive thin film, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film.

31. (Withdrawn) A stencil mask manufacturing method comprising:

forming a concave portion in which an insulating film is exposed in a region corresponding to a second region of a substrate of an SOI substrate which includes the substrate, an insulating film formed on the substrate, and a conductive thin film with a first region and the second region formed on the insulating film;

removing the exposed insulating film;

forming a conducting member in the concave portion, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film;

making openings in a region corresponding to the first region of the conductive thin film; and

removing the substrate and insulating film corresponding to the first region.

32. (Withdrawn) A mask forming substrate manufacturing method comprising:

forming a concave portion by removing a substrate and an insulating film corresponding to a second region of an SOI substrate which includes the substrate, the

insulating film formed on the substrate, and a conductive thin film formed on the insulating film and having a first region as an opening formation region and the second region around the first region; and

forming a conducting member in the concave portion, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film.

33. (Withdrawn) A stencil mask manufacturing method comprising:

making a first opening by removing a conductive thin film and an insulating film corresponding to a second region of an SOI substrate which includes a substrate, the insulating film formed on the substrate, and the conductive thin film with a first region and the second region formed on the insulating film;

forming a conducting member in the entire surface of the conductive thin film and in the first opening, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film;

making a second opening by removing the conducting member and the conductive thin film corresponding to the first region; and

forming a support by removing the substrate and insulating film corresponding to the first region.

34. (Withdrawn) A mask forming substrate manufacturing method comprising:

making a first opening by removing a conductive thin film and an insulating film corresponding to a second region of an SOI substrate which includes a substrate, the insulating film formed on the substrate, and the conductive thin film with a first region and the second region formed on the insulating film; and

forming a conducting member in the entire surface of the conductive thin film and in the first opening, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film.

35. (Currently Amended) A mask forming substrate comprising:

a conductive thin film having ~~an inside~~ a first region as a opening formation region and ~~an outside~~ a second region peripheral of the first region;

an insulating film formed on the conductive thin film;

a conductive support formed on the insulating film;

an opening ~~in the outside region~~ formed in the conductive thin film corresponding to a part of the second region and the insulating film; and

a conductive member ~~which is~~ formed in the opening ~~and which connects,~~ the conductive member connecting the conductive thin film and the conductive support electrically.

36. (New) The stencil mask according to claim 1, wherein the first openings are surrounded by the third opening.